

SILICON PNP TRANSISTOR EPITAXIAL PLANAR TYPE (PCT PROCESS)

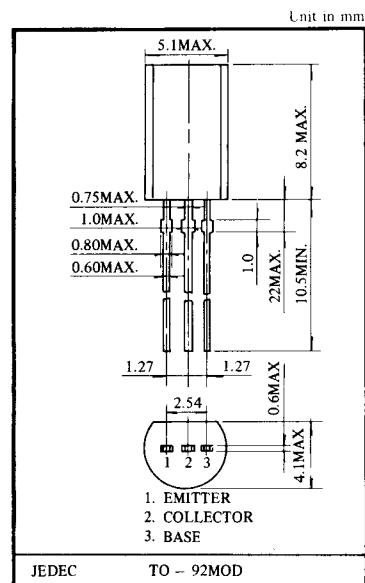
2SA1273

APPLICATIONS

- Audio Power Amplifier Applications.

FEATURES

- Complementary to 2SC 3205
and 3 Watts Output Applications.



■ MAXIMUM RATINGS (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT	CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CB0}	-30	V	Emitter Current	I_E	2	A
Collector-Emitter Voltage	V_{CE0}	-30	V	Collector Dissipation	P_C	1	W
Emitter-Base Voltage	V_{EB0}	-5	V	Junction Temperature	T_j	150	℃
Collector Current	I_C	-2	A	Storage Temperature	T_{stg}	-55~150	℃

■ ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = -30V, I_E = 0$	—	—	-100	nA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -5V, I_C = 0$	—	—	-100	nA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -10mA, I_B = 0$	-30	—	—	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -1mA, I_C = 0$	-5	—	—	V
DC Current Gain	h_{FE}	$V_{CE} = -2V, I_C = -500mA$	100	—	320	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -1.5A, I_B = -0.03A$	—	—	-2.0	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = -2V, I_C = -500mA$	—	—	-1.0	V
Transition Frequency	f_T	$V_{CE} = -2V, I_C = -500mA$	—	120	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$	—	48	—	pF

■ NOTE: According to h_{FE} , Classified as follows.

0	100-200	Y	160-320
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